RoHS

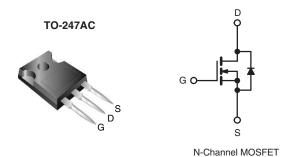
COMPLIANT

HALOGEN FREE



D Series Power MOSFET

PRODUCT SUMMARY			
V _{DS} (V) at T _J max. 450			
R _{DS(on)} max. at 25 °C (Ω)	V _{GS} = 10 V 0.17		
Q _g max. (nC)	88		
Q _{gs} (nC)	12		
Q _{gd} (nC)	23		
Configuration	Single		



FEATURES

 Halogen-free According to IEC 61249-2-21 Definition



- Low Area Specific On-Resistance
- Low Input Capacitance (Ciss)
- Reduced Capacitive Switching Losses
- High Body Diode Ruggedness
- Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
 - Low Cost
 - Simple Gate Drive Circuitry
 - Low Figure-of-Merit (FOM): Ron x Qg
 - Fast Switching
- Compliant to RoHS Directive 2011/65/EU

APPLICATIONS

- Consumer Electronics
 - Displays (LCD or Plasma TV)
- Lighting
- Industrial
 - Welding
 - Induction Heating
 - Motor Drives
 - Battery Chargers
- SMPS

ORDERING INFORMATION		
Package	TO-247AC	
Lead (Pb)-free	SiHG25N40D-E3	
Lead (Pb)-free and Halogen-free	SiHG25N40D-GE3	

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	400	
Gate-Source Voltage		V	± 30	V
Gate-Source Voltage AC (f > 1 Hz)		V _{GS}	30	
Continuous Drain Current (T _{.1} = 150 °C)	V_{GS} at 10 V $T_{C} = 25 ^{\circ}C$ $T_{C} = 100 ^{\circ}C$		25	
Continuous Drain Current (1j = 150 °C)	$T_C = 100 ^{\circ}$ C	I _D	16	Α
Pulsed Drain Current ^a		I _{DM}	78	
Linear Derating Factor			2.2	W/°C
Single Pulse Avalanche Energyb		E _{AS}	556	mJ
Maximum Power Dissipation		P _D	278	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 150	°C
Drain-Source Voltage Slope T _J = 125 °C		dV/dt	24	V/ns
Reverse Diode dV/dtd		av/di	0.6	
Soldering Recommendations (Peak Temperature)	for 10 s		300°	°C

- a. Repetitive rating; pulse width limited by maximum junction temperature.
- b. V_{DD} = 50 V, starting T_J = 25 °C, L = 2.3 mH, R_g = 25 Ω , I_{AS} = 17 A.
- c. 1.6 mm from case.
- d. $I_{SD} \le I_D$, starting $T_J = 25$ °C.



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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R _{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	C/ VV

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•	•	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0 V, I _D = 250 μA	400	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference	e to 25 °C, I _D = 250 μA	=.	0.5	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} :	= V _{GS} , I _D = 250 μA	3	-	5	V
Gate-Source Leakage	I _{GSS}		V _{GS} = ± 30 V	-	-	± 100	nA
7 0 1 1/1 5 1 0 1		V _{DS} :	= 400 V, V _{GS} = 0 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 320 \	V, V _{GS} = 0 V, T _J = 125 °C	-	-	10	μA
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 13 A	-	0.14	0.17	Ω
Forward Transconductance	9 _{fs}	V _{DS}	= 50 V, I _D = 13 A	-	7.4	-	S
Dynamic						•	
Input Capacitance	C _{iss}		$V_{GS} = 0 V$	-	1707	-	
Output Capacitance	C _{oss}	1	V _{GS} = 0 V, V _{DS} = 100 V,		177	-	pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		-	19	-	
Total Gate Charge	Qg			-	44	88	nC
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V	$I_D = 13 \text{ A}, V_{DS} = 320 \text{ V}$	-	12	-	
Gate-Drain Charge	Q_{gd}	1	-	23	-]	
Turn-On Delay Time	t _{d(on)}			-	21	42	
Rise Time	t _r	V _{DD} :	= 320 V, I _D = 13 A,	-	57	86	1
Turn-Off Delay Time	t _{d(off)}	$V_{GS} = 10 \text{ V}, R_g = 24.6 \Omega$		-	40	80	ns
Fall Time	t _f		•	-	37	74	1
Gate Input Resistance	R_g	f = 1	MHz, open drain	-	1.8	-	Ω
Drain-Source Body Diode Characteristic	S						
Continuous Source-Drain Diode Current	I _S	MOSFET sym	MOSFET symbol showing the		-	24	_
Pulsed Diode Forward Current	I _{SM}	integral reverse p - n junction diode		-	-	78	A
Diode Forward Voltage	V _{SD}	T _J = 25 °	C, I _S = 13 A, V _{GS} = 0 V	-	-	1.2	V
Reverse Recovery Time	t _{rr}			-	353	-	ns
Reverse Recovery Charge	Q _{rr}		5 °C, I _F = I _S = 13 A,		4.4	-	μC
Reverse Recovery Current	I _{RRM}	dI/dt = 100 A/μs, V _R = 20 V		_	24	_	Α



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

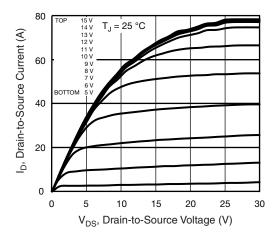


Fig. 1 - Typical Output Characteristics

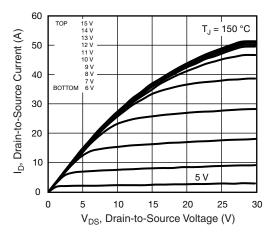


Fig. 2 - Typical Output Characteristics

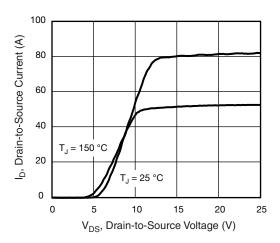


Fig. 3 - Typical Transfer Characteristics

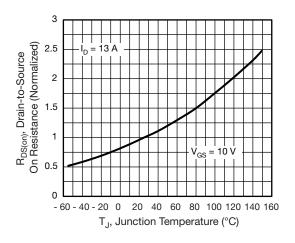


Fig. 4 - Normalized On-Resistance vs. Temperature

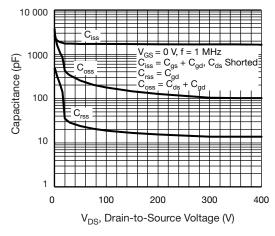


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

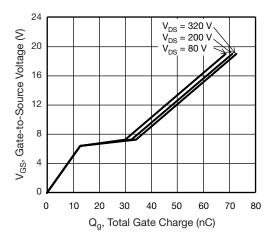


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



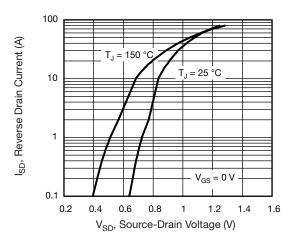


Fig. 7 - Typical Source-Drain Diode Forward Voltage

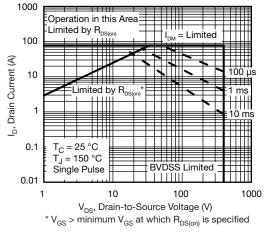


Fig. 8 - Maximum Safe Operating Area

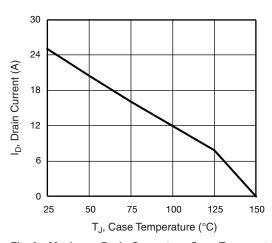


Fig. 9 - Maximum Drain Current vs. Case Temperature

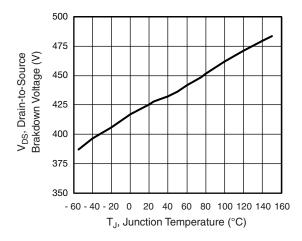


Fig. 10 - Temperature vs. Drain-to-Source Voltage

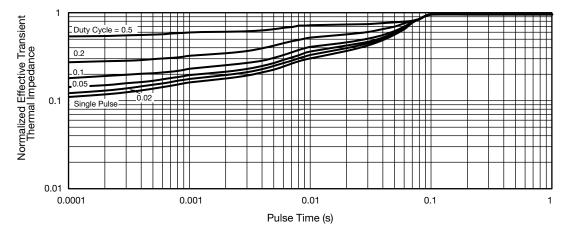


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case



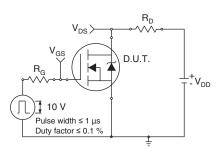


Fig. 12 - Switching Time Test Circuit

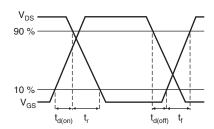


Fig. 13 - Switching Time Waveforms

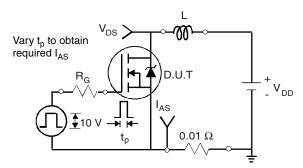


Fig. 14 - Unclamped Inductive Test Circuit

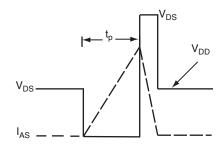


Fig. 15 - Unclamped Inductive Waveforms

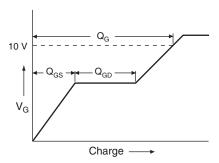


Fig. 16 - Basic Gate Charge Waveform

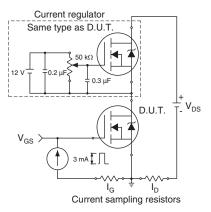
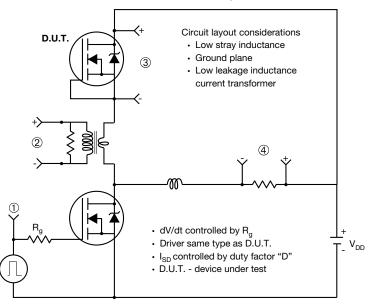


Fig. 17 - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit



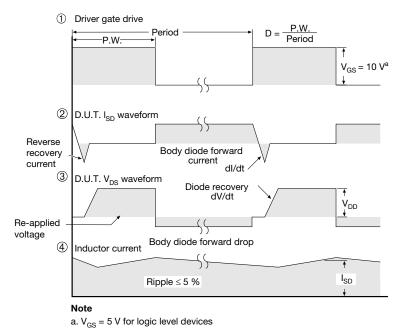


Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91484.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	0.254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.2	54	
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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